

# Low&Ultra High speed fast recovery diode series

After favorable response to ROHM's low VF series, we will lead the market for ultra high speed rectifier diodes.

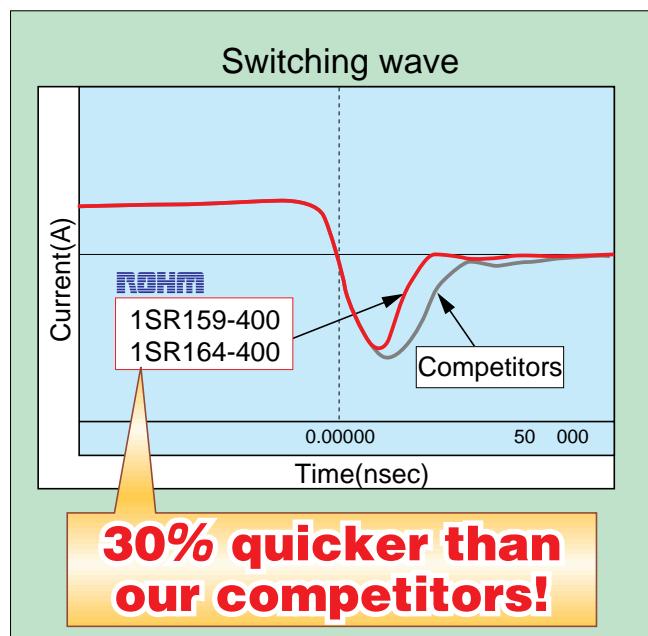
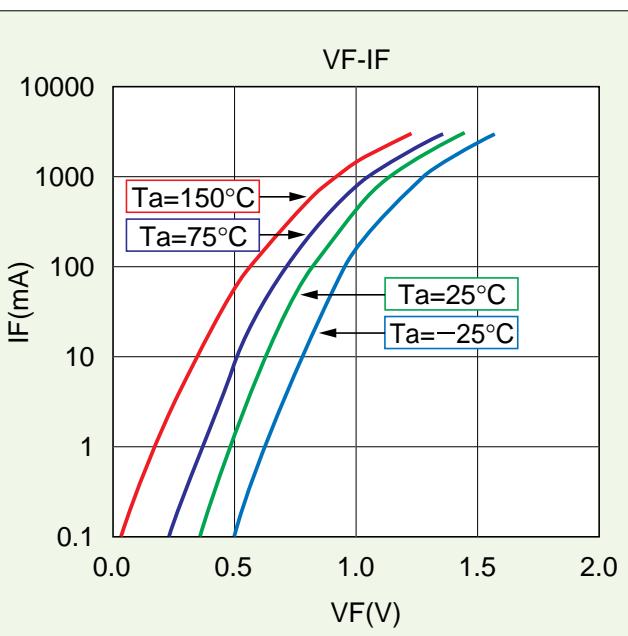
Our new diodes will be low loss and have low VF and ultra high speed FRD.

## Characteristic

Switching speed (**10nsec typ.**)  
Low VF (**1.10V typ.**)

Low loss.  
(Soft recovery)

TYPE.(taping)	Package	Io/VRM	V <sub>F</sub> (at IF)	t <sub>rr</sub> (0.5/1.0A)	Dimension	
1SR159-400	PMDS (4526)	1A/400V	1.10V typ (1.0A)	10 nsec typ.		
1SR159-200		1A/200V	Mass production is available			
1SR159-600		1A/600V	Under development			
1SR164-400		1A/400V	1.10V typ (1.0A)	10 nsec typ.		



## Ultra first recovery diode(Silicon epitaxial planer)

1SR159-400

Low loss

**APPLICATION**

High-speed switching

**FEATURE**

- Small power mold type(PMDS)
- Low VF
- High-speed switchig, Soft recovery
- Low switching loss

**Mass per piece**

69mg/pcs

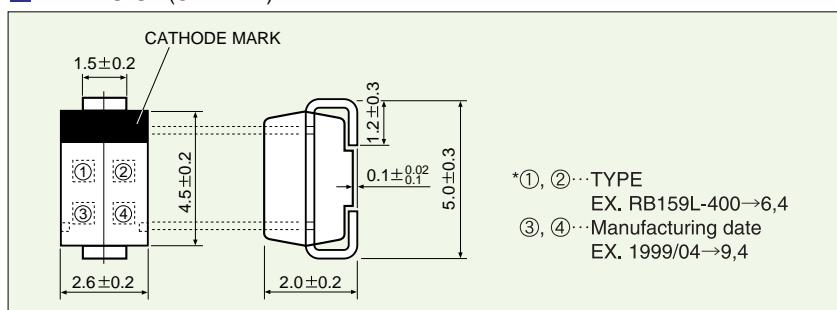
**ABSOLUTE MAXIMUM RATING(Ta=25°C)**

Characteristic	Symbol	Limits
Reverse voltage(repetitive peak)	VRSM	400V
Reverse voltage(DC)	VRM	400V
Average rectified forward current	Io	1A
Forward current surge peak(60Hz·1∞)	IFSM	20A
Junction temperature	Tj	150°C
Storage temperature	Tstg	-40~150°C

**ELECTRICAL CHARACTERISTIC(Ta=25°C)**

Characteristic	Symbol	Test condition	Standard	Maximum
Forward current	VF	IF=1.0A	1050mV	1200mV
Reverse current	IR	VR=400V	0.7μA	10μA
Switching time	Tr	IF=0.5A IR=1.0A Irr=0.25*IR	10nsec	25nsec

\*Please pay attention to static electricity when handing.

**DIMENSION(UNIT:mm)**

## Ultra first recovery diode(Silicon epitaxial planer)

1SR164-400

Low loss

**APPLICATION**

High-speed switching

**FEATURE**

- Mold type(MSR)
- Low VF
- High-speed switchig, Soft recovery
- Low switching loss

**Mass per piece**

190mg/pcs

**ABSOLUTE MAXIMUM RATING(Ta=25°C)**

Characteristic	Symbol	Limits
Reverse voltage(repetitive peak)	VRSM	400V
Reverse voltage(DC)	VRM	400V
Average rectified forward current	Io	1A
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